Conductance of a Quantum Point Contact in the presence of a Scanning Probe Microscope Tip

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U sing the recursive G reen's function technique, we study the coherent electron conductance of a quantum point contact in the presence of a scanning probe m icroscope tip. Im ages of the coherent fringe inside a quantum point contact for di erent widths are obtained. It is found that the conductance of a speci c channel is reduced while other channels are not a ected as long as the tip is located at the positions corresponding to that channel. Moreover, the coherent fringe is smoothed out by increasing the temperature or the voltage across the device. Our results are consistent with the experiments reported by Topinka et al. (Science 289, 2323 (2000)).

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Quantum point contacts (QPCs) formed in twodim ensional electron gases (2D EGs) have attracted signi cant attention for the past two decades.1;2 Since the discovery of the conductance quantization in these structures, QPCs have been widely used in a variety of investigations, including transport through quantum dots, the quantum Halle ect, magnetic focusing, and the Aharonov-Bohm e ect. Also, with the rapid developm ent on scanning probem icroscope (SPM) techniques, it is possible to im age current directly to study many rem arkable phenom ena, including quantum corrals, electron ow through nanostructures,4 charge distribution and photoactivity of dopant atom s_{r}^{5} and spectra of m etallic nanoclusters. Since the QPC plays such an im portant role in mesoscopic devices, it is an ideal system to be studied by the SPM techniques.

Very recently, Topinka et al. have directly imaged the electron ow from the QPC by scanning a negatively charged SPM tip above the surface of the device and measuring the position-dependent conductance simultaneously.7;8 In the experiment, as the width of the QPC increases, the conductance increases in quantized steps of 2e²=h, as was also reported in other experiments. 1 Besides, several new and interesting features were observed. W idening of the angular structure of electron ow has been clearly seen as the QPC channel becom eswider. A nother feature of their im ages is the appearance of fringes spaced by half the Ferm iwavelength transverse to the electron ow, which clearly shows the character of coherent quantum interference. The above fringes are thermally smeared out by increasing the effective electron temperature. Moreover, when the tip is placed such that it interrupts the ow from particular modes of the QPC, a reduction can be observed in the conductance of those channels, while other channels are not a ected. 7 On the other hand, it is also found that, in contrary to intuitions, the electron ow from the

point contact form s narrow branching strands instead of smoothly spreading fans. 8

Using the recursive G reen's function technique, in this paper, we study theoretically a mesoscopic structure similar to the experimental one. Our numerical results are able to explain the experimental nding in Refs. 7,8. Therefore, the recursive G reen's function technique seems to be a suitable method to study the coherent electron conductance in such a mesoscopic system.

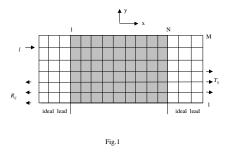


FIG. 1. Schematic diagram of the system.

We consider a negatively charged SPM tip capacitively coupled to the 2DEG where the QPC is formed. The effect of SPM tip is that, the conductance will decrease if the tip is positioned over regions with high electron ow from the QPC, while it will be less modiled if the tip is at low electron ow regions. The electron ow can be imaged by scanning the tip over the two-dimensional surface. Two contributions to the potential in the 2DEG region should be taken into account. One is

from the negatively charged gates that de ne the QPC, which we model with the Buttiker saddle-point potential $U(x;y) = V_g \text{ m } !_x^2 x^2 = 2 + \text{m } !_y^2 y^2 = 2 \text{ w ith } V_g \text{ as the gate}$ voltage, m as the electron e ective m ass and ! x;v as the strength of the lateral con nem ent. This potential is a practical candidate to reproduce the quantized conductance of a QPC. 9 The other is a Lorentzian type potential induced by the SPM tip, 10 which we approximate as a delta function in the present work: $V_{SPM} = V_t$ (r r_t), where r_t denotes the position of the tip, and V_t is a negative constant. It is worth noting that the numerical results obtained with the simple delta potential are consistent the experim ental results.7;8

We use a 2D square lattice model to describe the QPC system. The sites of the lattice are denoted as (na; ma) with a to be set equal to unit, n = 1; 2; ...; Nand m = 1;2;::; M . The lattice may be divided into three regions, as shown in Fig.1. The shadowed central zone is a mesoscopic structure with a Buttiker saddlepoint potential and scanned by a SPM tip. Both sides of the structure are assumed to be connected with sem iin nite ideal leads to simplify scattering boundary conditions. The one-electron tight-binding Ham iltonian of the system takes the form 11

$$H = \begin{bmatrix} X \\ n_{n,m} & j_{n,m} & j_{n,m} \end{bmatrix}$$

$$X \\ \text{(tjn;m ihn 1;m j+ tjn;m ihn;m 1j+ H C:); (1)}$$

where $t = h^2 = 2m$ a² and $\dot{\eta}$; m i is a orthonormal set in the lattice sites (n;m). The on-site energy in the central zone is given by $"_{n,m} = U_{n,m} + V_{SPM} + 4t$. Then the Ham iltonian for this region reads

$$H_{c} = \int_{n=1}^{X^{N}} \dot{p}_{n} H_{n} (n j + \int_{n=1}^{N_{X}} (\dot{p}_{n}) H_{n;n+1} (n + 1 j + H : C :);$$

where jn) denotes the set of M ket vectors belonging to the n-th cell, and

$$H_{n} \quad H_{n,n} = \begin{cases} 2 & \mathbf{m}_{n;1} & t & 0 & 0 \\ 6 & t & \mathbf{m}_{n;2} & t & 0 \\ 6 & 0 & t & \mathbf{m}_{n;3} & 0 \\ 2 & \vdots & \vdots & \ddots & \vdots \\ 0 & 0 & 0 & 0 & 0 \end{cases}$$

$$(H_{n;n} _{1})_{pp^{0}} = (H_{n;n+1})_{pp^{0}} = t_{pp^{0}} (p;p^{0} = 1; ...;M)$$
:

The Hamiltonians for the two ideal leads have the same form as Eq.(2), but with dierent sum ming regions (1 < n < 1 at the left lead and N < n < 1 at the right lead) and $"_{n,m} = 4t$.

U sing the recursive G reen's function technique, the transmission amplitude for the incident channel land outgoing channelj is found to be^{11;12}

where v_j = @E =h@k_j with $_PE$ = 4t 2t($\cos k_j$ + $\cos j$ =(M + 1)), (E) = 2it $_{l=1}^M$ Q $_1\sin k_1$ with

$$(Q_1)_{pp^0} = \frac{2}{M+1} \sin \frac{1 p}{M+1} \sin \frac{1 p^0}{M+1}; (p;p^0 = 1; jM):$$

The set of vectors $_{k_1}^+$ are the duals of the set $_{k_1}$, de ned by $k_1 k_1 = j_1$ where

$$r = \frac{r}{\frac{2}{M+1}} (\sin \frac{j}{M+1}; ...; \sin \frac{jm}{M+1}; ...; \sin \frac{jM}{M+1})^{T_r}$$

with T_r as the transposition of matrix. $G_{N+1;0}$ is the retarded G reen's function for the scattering region between two ideal leads, which can be obtained by a set of recursion formulas in a matrix form, 12;13

$$G_{n^{0}+1;0} = tg^{n^{0}+1}G_{n^{0};0}; (0 n^{0} N)$$

$$g^{n^{0}+1} = (E f_{n^{0}+1}^{0} t^{2}g^{n^{0}})^{1}; (5)$$

$$q^{n^0+1} = (E \quad \mathbb{F}_{n^0+1} \quad t^2 q^{n^0})^{-1};$$
 (5)

(= 0; N + 1).

At nite tem perature T, the conductance through a 2D (tjn; m ihn 1; m j+ tjn; m ihn; m 1j+ H Ω :); (1) m esoscopic structure is given by the Landauer-Buttiker form $u \ln^{14}$

G (T) =
$$\frac{2e^2}{h} \frac{X}{1;j} = 0$$
 $T_{1j} \frac{\text{@f (E;T)}}{\text{@E}} \text{dE;}$ (6)

where $T_{lj} = \int_{lj} \hat{f}$ is the transmission coe cient, and $f(E;T) = [1 + \exp(E \quad E_F) = k_B T]^1$ is the Ferm i-D irac distribution with E_F as the Fermi energy and k_B as the Boltzm ann constant. O byjously, at zero tem perature Eq.(6) reduces to $G = 2e^2 = h$ fl;jg Tlj.

The above formulas are valid under the assumption that the voltage across the device is low. High voltage will raise the energies of electrons owing from the QPC. Thus, as shown by van W ees et al., the conductance at a nite voltage V has a similar behavior to that with a nite tem perature e ect, and is given by

$$G (V) = \frac{2e}{h} \frac{1}{V} X^{Z_{E_F} + eV} T_{1j} dE :$$
 (7)

In the following we calculate numerically the conductance of a Q P C system w ith the size N = 15 and M = 11.We set t and the lattice constant a as the units of energy and length, respectively. In order to obtain wellpronounced quantized plateaus with the Buttiker saddlepoint potential, we choose $!_{v} = 2!_{x}$, $E_{F} = 2t$, and $V_{t} = 1:5t.$

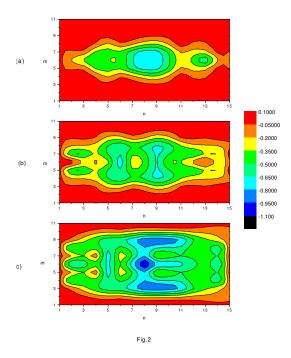


FIG. 2. Im ages of electron ow across a QPC at zero temperature and low voltage for three dierent widths corresponding to (a) the rst conductance plateau, $V_g=0.7E_F$; (b) the second plateau, $V_g=0.4E_F$; (c) the third plateau, $V_g=0.2E_F$. The color scale shows the change G=G G G in QPC conductance as the tip is scanned above the device.

At zero tem perature and low voltage lim it, im ages of electron ow from the 2D surface of the QPC are plotted in Fig.2. The gate voltage V_{α} is chosen to ensure Fig 2 (a) - (c) correspond to the rst, the second and the third conductance plateau of the QPC, respectively. It is seen clearly that a new electron ow pattern appears when a higher mode is opened (then the conductance of the QPC rises to another plateau) by decreasing the gate voltage. This feature agrees with the result reported in Ref.7: electronic wavefunctions inside the QPC have N maximawhenQPC has N conductance modes. Note that the images do not turn into smoothly spreading fans as the electrons ow across the QPC from the left to the right. Instead, they form branching strands which are relatively narrower. In fact, even the width of the sample decreases to M = 6 in the calculation, the im ages change little (not shown here). It is not surprising that strands are form ed in our model since the electrons are laterally con ned. On the other hand, a sim ilar but also striking phenom enon is reported in Ref.8, where the strands were found in regions far away from the point contact. So we can see that the electron path has a rare probability to pass through the edge regions of the sam ple, and thus the im purity density and the boundary scattering in these regions are less relevant to the conducting property of the QPC. Moreover, the fringe structures due to the alternating constructive and destructive interference of electrons are evident in Fig.2, though the distribution is not so hom ogeneous when compared with the experiments. This inhom ogeneity induced from the varieties of electron wavelength inside the QPC is the main dierence between the structure of fringe inside and outside QPC. It is worth pointing out that the fringes directly demonstrate the coherent character of electron ow in QPC.

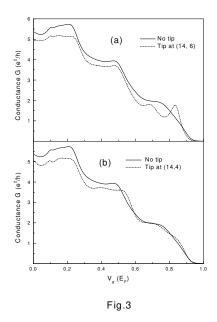


FIG. 3. The conductance plateaus of the QPC for the selective e ect of the SPM tip. The solid line represents the curve without SPM tip, and the dash line is the curve with the SPM placed over certain position such that it blocks the electron ow from (a) the rstmode, or (b) the second mode.

M eanwhile, we also note that the angular structures in these electron ow patterns are quite di erent from each other, especially for the rst and second modes. For the rst mode, the pattern contains one branch only, while there are two branches for the second mode. So there are some regions in the 2D surface where the distribution of electrons at one mode make no contribution to the other mode. As reported in experiments, when the SPM tip is placed over these regions, only the ow from particular channels of the QPC are changed, while other channels are not a ected. This phenomenon is clearly manifested in Fig.3, where the quantized G V_g curves of the QPC with or without the SPM tip are plotted. From the comparison between the behaviors of the solid line and the

dash line in Fig.3(a), we can see that when the tip is placed at the central axis of the QPC where the electrons from the rstm ode travelthrough, the heights of all plateaus are reduced. But the height di erence between each pair of neighboring plateaus remains to be $2e^2$ =h, except for that between the rst plateaus and the 0-axis. In Fig.3(b), the SPM tip is positioned o the central axis. A coording to Fig.2(a) and (b), we can learn that this position corresponds to G 0 in the rstm ode, and it only a ects the second mode. Thus in Fig.3(b) it is shown that the rst conductance plateau is almost unchanged, and the second and other higher plateaus are lowered. A gain, the height di erence between the second and the third plateaus still remains to be $2e^2$ =h.

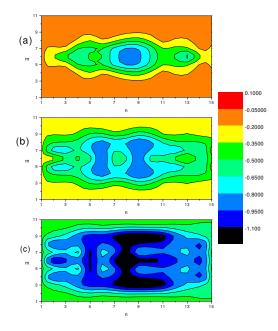


Fig.4(a,b,c)

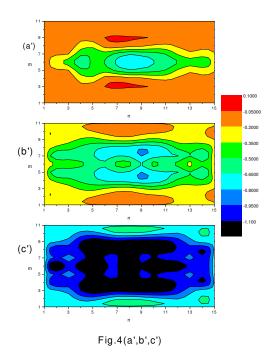


FIG. 4. E ect of electron heating on images of ow. (a-c) show electron ow for the rst, second and third conductance plateaus under the voltage eV = 0.05t. (a $^{\circ}$ c $^{\circ}$) show corresponding images for higher voltage eV = 0.2t. O ther parameters are the same as those in Fig.2.

The electron ows under the nite voltages across the QPC are imaged in Fig.4, where (a c) are at a low voltage (eV = 0.05t) and (a⁰ c⁰) are at a high voltage (eV = 0.2t). Comparing it with Fig.2, we see that the pattern still rem ains the same in each mode, but the values of G is no longer so severely uctuated when the voltage is raised. A m ore im portant characteristic of voltage e ect is that fringe structure would gradually disappear as the voltage rises. A ctually, we not that the three conductance modes gradually merge into one conductance mode, which implies that the quantized plateaus also disappear as the voltage is increased. The origin of the fringes is the coherent quantum interference. Since the fringes are less perceptible as the uctuation of G becomes pacied, it is manifested that the consequence of using e ectively hotter electrons is to smear out the coherence among electrons. The above properties are sim ilar for elevating tem perature as the physical e ects of tem perature and voltage are the same here. 15 C learly, the voltage e ect addressed here is in qualitative agreem ent with the experim ental observation.

In conclusion, we have calculated the conductance of a QPC in the presence of the SPM tip by the recursive Green's function technique. The numerical results are able to explain the experimental results in Refs.7,8.

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Beenakker, J.G.W illiam son, and C.T.Foxon, Phys.Rev. B 43, 12431 (1991).

¹ B.J.van Wees, H.van Houten, C.W.J.Beenakker, J.G. William son, L.P.Kouwenhoven, D.van der Marel, and C. T.Foxon, Phys.Rev.Lett. 60, 848 (1988); D.A.Wharam, T.J.Thomton, R.Newbury, M.Pepper, H.Ahmed, J.E. F.Frost, D.G.Hasko, D.C.Peacock, D.A.Ritchie, and G.A.C.Jones, J.Phys.C 21, L209 (1988).

 $^{^{2}}$ C.W.J.Beenakker and H.van Houten, Solid State Phys. 44,1 (1991).

³ M.F.Crom m ie, C.P.Lutz, and D.M. Eigler, Science 262, 218 (1993); E.J.Heller, M.F.Crom m ie, C.P.Lutz, and D.M. Eigler, Nature 369, 464 (1994); H.C.M anoharan, C.P.Lutz, and D.M. Eigler, Nature 403, 512 (2000).

⁴ M. A. Eriksson, R. G. Beck, M. Topinka, J. A. Katine, R. M. Westervelt, K. L. Campman, and A. C. Gossard, Appl. Phys. Lett. 69, 671 (1996); R. Crook, C. G. Smith, C. H. W. Barnes, M. Y. Simmons, and D. A. Ritchie, J. Phys. Cond. Matt. 12, L167 (2000).

⁵ M.J. Yoo, T.A. Fulton, H.F. Hess, R.L. Willett, L.N. Dunkleberger, R.J. Chichester, L.N. Pfei er, and K.W. West, Science 276, 579 (1997).

⁶ L. Gurevich, L. Canali, and L. P. Kouwenhoven, Appl. Phys. Lett. 76, 384 (2000).

⁷ M. A. Topinka, B. J. LeRoy, S. E. J. Shaw, E. J. Heller, R. M. Westervelt, K. D. Maranowski, and A. C. Gossard, Science 289, 2323 (2000).

⁸ M. A. Topinka, B. J. LeRoy, R. M. Westervelt, S. E. J. Shaw, R. Fleischmann, E. J. Heller, K. D. Maranowski, and A. C. Gossard, Nature 410, 183 (2001).

⁹ M .Buttiker, Phys.Rev.B 41, 7906 (1990).

M.A. Eriksson, R.G. Beck, M.A. Topinka, J.A. Katine, R.M. Westervelt, K.L. Campman, and A.C. Gossard, Superlattices Microstruct. 20, 435 (1996).

¹¹ S.L.Zhu, Z.D.W ang, and L.Hu, J.Appl.Phys.91, 6545 (2002).

¹² T. Ando, Phys. Rev. B 44, 8017 (1991); S. Sanvito, C. J. Lambert, J. H. Je erson, and A. M. Bratkovsky, ibid. 59, 11936 (1999).

¹³ P.A. Lee and D.S. Fisher, Phys. Rev. Lett. 47, 882 (1981); L. Schweitzer, B. Kramer, and A. MacKinnon, J. Phys. C 17, 4111 (1984); A. MacKinnon, Z. Phys. B 59, 385 (1985).

¹⁴ R.Landauer, IBM J.Res.Dev.1, 223 (1957); M.Buttiker, Phys.Rev.Lett.57, 1761 (1986).

B.J. van W ees, L.P.K ouwenhoven, E.M.M.W illems, C. J.P.M. Harmans, J.E.Mooij, H. van Houten, C.W.J.